

SPECIFICATION OF LED CHIP

C630-30W

[Orange]

1) Commodity Type and Physical Characteristics.

1. Material	InGaAlP	
2. Electrode	Top Side P (anode)side	:Au Alloy/ Pad
	Bottom Side N (cathode)side	:Au Alloy
3. Electrode Pattern		Fig.1
4. Chip Size		Fig.2
5. Chip Thickness		Fig.2
6. Emission Area		Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _f =20mA		2.2	2.6	V
Reverse Current	I _r	V _r =5V			10	uA
Brightness	I _v	I _f =20mA		150		mcd
Power Intensity	P _o	I _f =20mA		5		mW
Peak Wavelength	λ _p	I _f =20mA	630	635	640	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		20		nm
RiseTime	t _r	I _f =20mA				ns
FallTime	t _f	I _f =20mA				ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

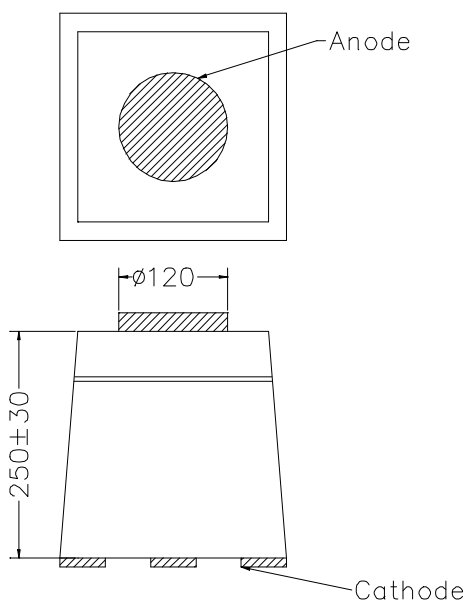
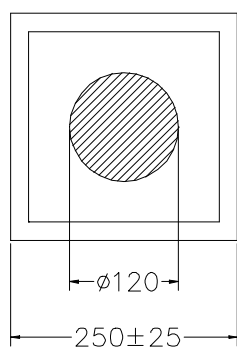


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area